

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-150V	180mΩ@-10V	-30A

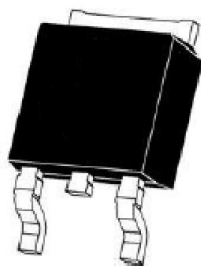
Feature

- Advanced trench technology
- Excellent $R_{DS(on)}$
- Low gate charge

Application

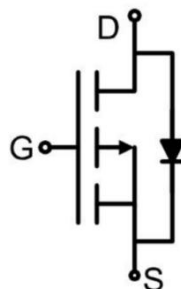
- Brushless motor
- Load switch
- Uninterruptible power supply

Package

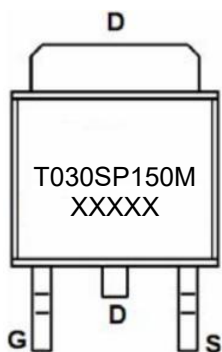


TO-252AB

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹⁾ (V _{GS} =-10V)	I _D	-30	A
Continuous Drain Current ¹⁾ (V _{GS} =-10V, T _c =70°C)	I _D (70°C)	-17.2	A
Pulsed Drain Current ²⁾	I _{DM}	-90	A
Single Pulse Avalanche Energy ³⁾	E _{AS}	250	mJ
Power Dissipation ⁴⁾	P _D	104	W
Thermal Resistance Junction to Case	R _{θJC}	1.2	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-150			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-150V, V _{GS} =0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-2	-3	-4	V
Drain-source on-resistance ²⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-10A		130	180	mΩ
Dynamic characteristics ⁵⁾						
Input Capacitance	C _{iss}	V _{DS} =-75V, V _{GS} =0V, f =1MHz		719		pF
Output Capacitance	C _{oss}			148		
Reverse Transfer Capacitance	C _{rss}			7		
Total Gate Charge	Q _g	V _{DS} =-75V, V _{GS} =-10V I _D =-10A		14.6		nC
Gate-Source Charge	Q _{gs}			4.8		
Gate-Drain Charge	Q _{gd}			4.5		
Turn-on delay time	t _{d(on)}	V _{DS} =-75V, V _{GS} =-10V R _L =7.5Ω, R _G =1Ω		10		nS
Turn-on rise time	t _r			6		
Turn-off delay time	t _{d(off)}			18		
Turn-off fall time	t _f			6		
Source-Drain Diode characteristics						
Diode Forward Current	I _S	T _C =25℃			-30	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =-5A			-1.2	V
Reverse recovery time	T _{rr}	I _F =-10A, di/dt =100 A/μs		62		nS
Reverse recovery charge	Q _{rr}			180		nC

Notes:

- 1) The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2) The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
- 3) The EAS data shows Max. rating. The test condition is V_{DD} = -50V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -10A.
- 4) The power dissipation is limited by 150°C junction temperature.
- 5) Guaranteed by design, not subject to production testing.

Typical Characteristics

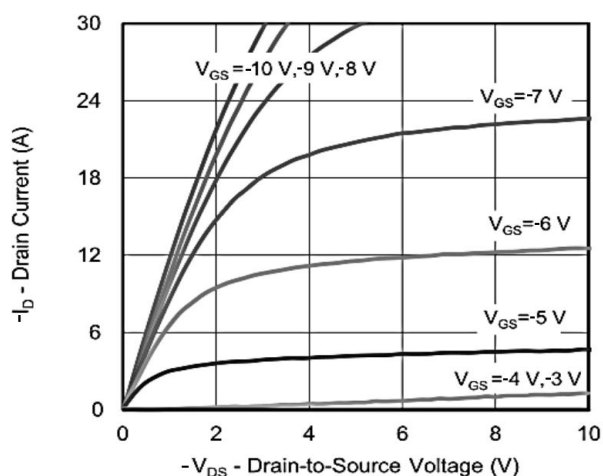


Fig1: Output Characteristics

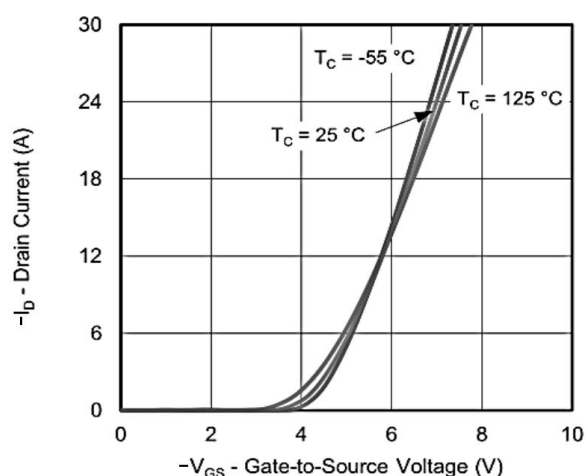


Fig2: Transfer Characteristics

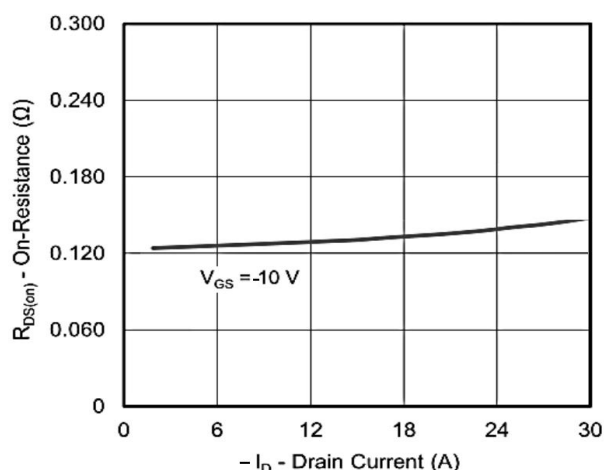


Fig3: On-Resistance vs. Drain Current and Gate Voltage

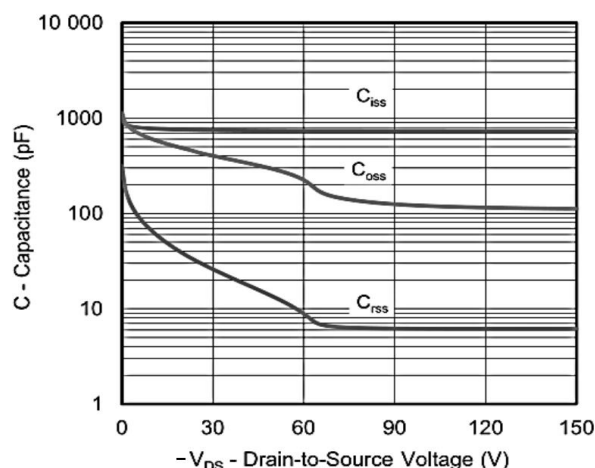


Fig4: Capacitance

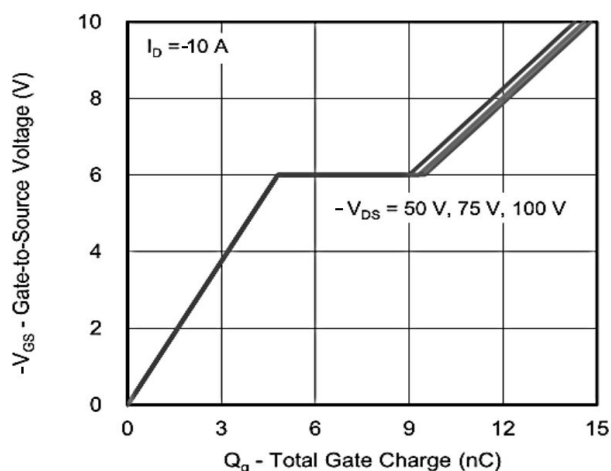


Fig5: Gate Charge

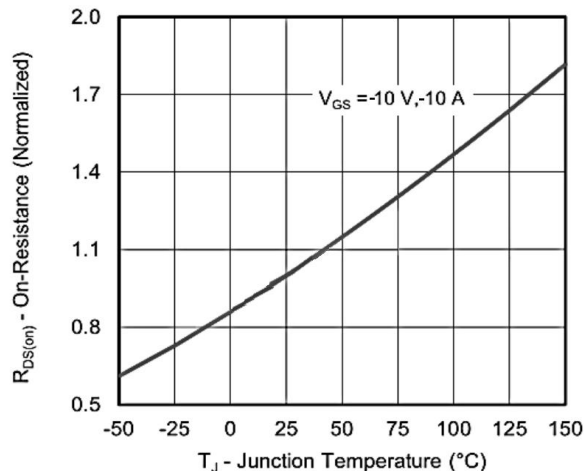


Fig6: On-Resistance vs. Junction Temperature

Typical Characteristics

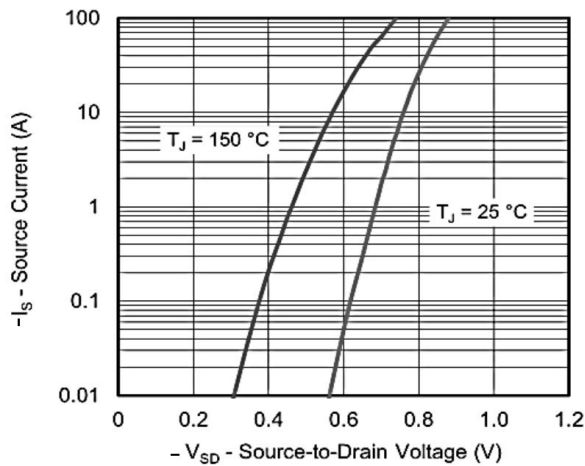


Fig7: Source-Drain Diode Forward Voltage

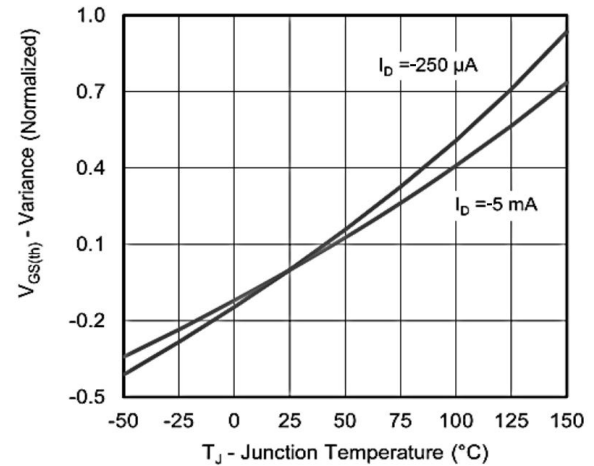


Fig8: On-Resistance vs. Gate-to-Source Voltage

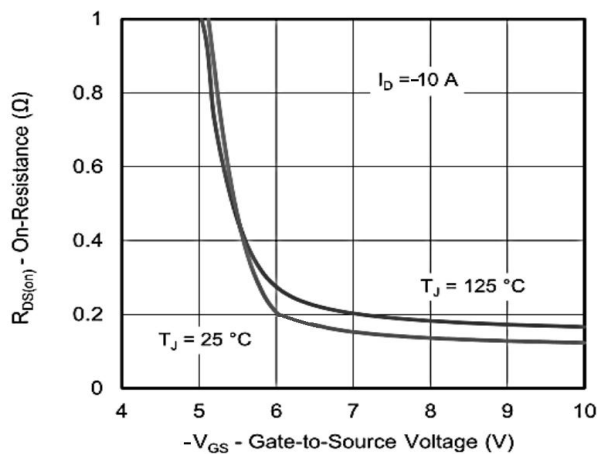


Fig9: Safe Operating Area, Junction-to-Ambient

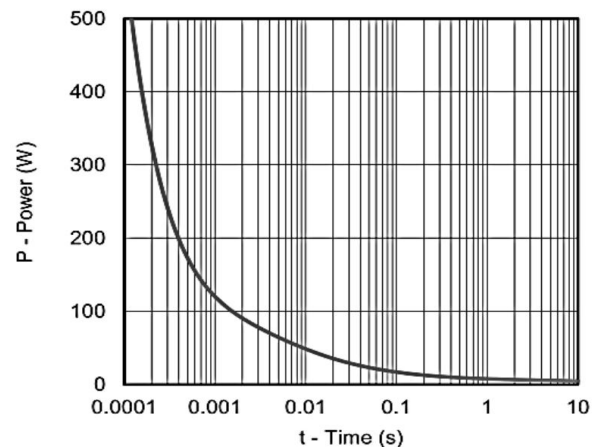


Fig10: Single Pulse Power, Junction-to-Ambient

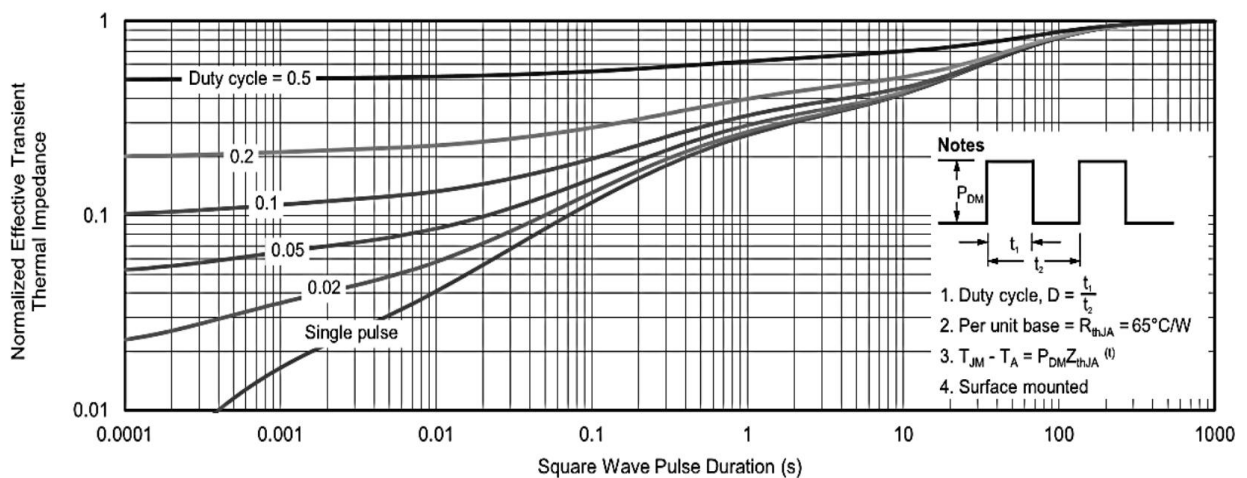
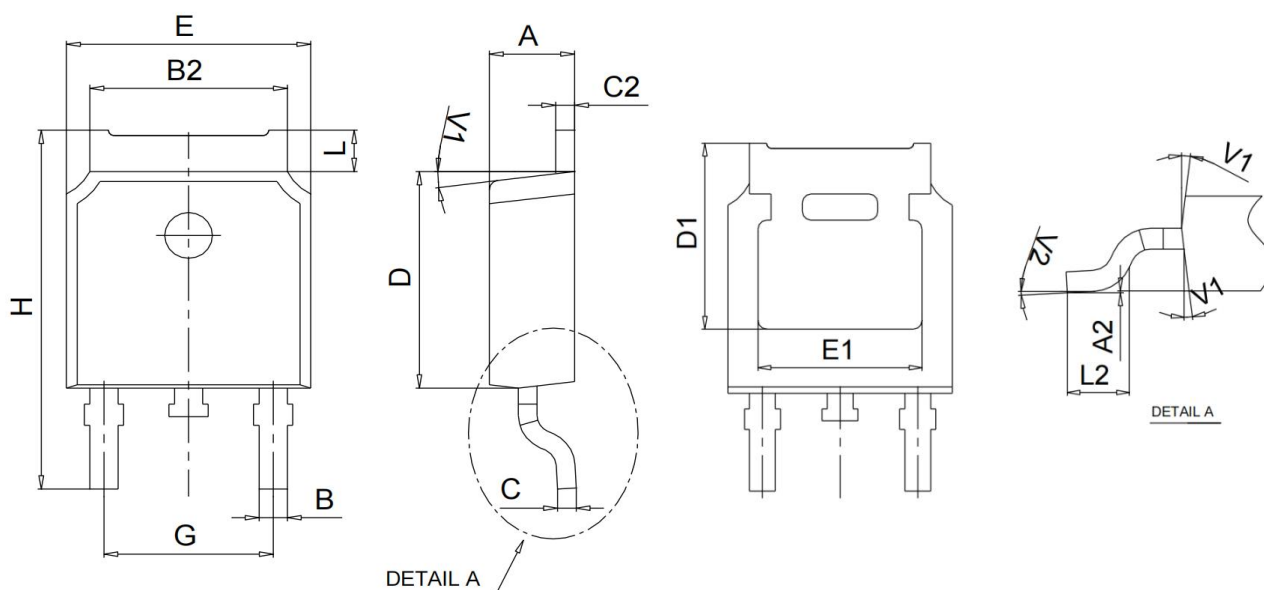


Fig10: Normalized Thermal Transient Impedance, Junction-to-Ambient

TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.100	2.500	0.083	0.098
A2	0.000	0.100	0.000	0.004
B	0.660	0.860	0.026	0.034
B2	5.180	5.480	0.202	0.216
C	0.400	0.600	0.016	0.024
C2	0.440	0.580	0.017	0.023
D	5.900	6.300	0.232	0.248
D1	5.300 REF.		0.209 REF.	
E	6.400	6.800	0.252	0.268
E1	4.630	-	0.182	-
G	4.470	4.670	0.176	0.184
H	9.500	10.700	0.374	0.421
L	1.090	1.210	0.043	0.048
L2	1.350	1.650	0.053	0.065
V1	7° BSC.		7° BSC.	
V2	0°	6°	0°	8°